

SNOSBT2D-MAY 2004-REVISED MAY 2004

## LM148/LM248/LM348 Quad 741 Op Amps

Check for Samples: LM148-N, LM248-N, LM348-N

### **FEATURES**

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- 741 Op Amp Operating Characteristics
- Class AB Output Stage—No Crossover Distortion
- Pin Compatible With the LM124
- Overload Protection for Inputs and Outputs
- Low Supply Current Drain: 0.6 mA/Amplifier

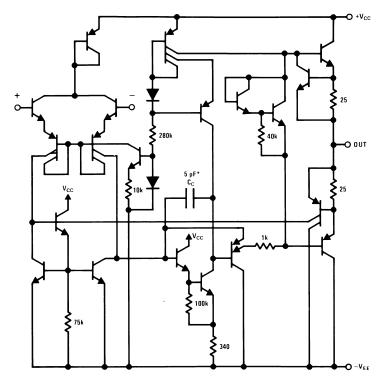
- Low Input Offset Voltage: 1 mV
- Low Input Offset Current: 4 nA
- Low Input Bias Current 30 nA
- High Degree of Isolation Between Amplifiers: 120 dB
- Gain Bandwidth Product
  - LM148 (Unity Gain): 1.0 MHz

#### DESCRIPTION

The LM148 series is a true quad 741. It consists of four independent, high gain, internally compensated, low power operational amplifiers which have been designed to provide functional characteristics identical to those of the familiar 741 operational amplifier. In addition the total supply current for all four amplifiers is comparable to the supply current of a single 741 type op amp. Other features include input offset currents and input bias current which are much less than those of a standard 741. Also, excellent isolation between amplifiers has been achieved by independently biasing each amplifier and using layout techniques which minimize thermal coupling.

The LM148 can be used anywhere multiple 741 or 1558 type amplifiers are being used and in applications where amplifier matching or high packing density is required. For lower power refer to LF444.

#### **Schematic Diagram**



\* 1 pF in the LM149

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### Absolute Maximum Ratings <sup>(1)(2)</sup>

		LM148	LM248	LM348	
Supply Voltage		±22V	±18V	±18V	
Differential Input Voltage		±44V	±36V	±36V	
Output Short Circuit Durati	on <sup>(3)</sup>	Continuous	Continuous	Continuous	
Power Dissipation (Pd at 2	5°C) and Thermal Resistance $(\theta_{jA})$ , <sup>(4)</sup>			·	
PDIP (NFF) P <sub>d</sub>		—	_	750 mW	
	θ <sub>JA</sub>	_	—	100°C/W	
CDIP (J) P <sub>d</sub>		1100 mW	800 mW	700 mW	
	θ <sub>JA</sub>	110°C/W	110°C/W	110°C/W	
Maximum Junction Tempe	rature (T <sub>jMAX</sub> )	150°C	110°C	100°C	
Operating Temperature Ra	nge	-55°C ≤ T <sub>A</sub> ≤ +125°C	−25°C ≤ T <sub>A</sub> ≤ +85°C	$0^{\circ}C \le T_A \le +70^{\circ}C$	
Storage Temperature Rang	ge	-65°C to +150°C	-65°C to +150°C	-65°C to +150°C	
Lead Temperature (Solder	ing, 10 sec.) Ceramic	300°C	300°C 300°C		
Lead Temperature (Solder	ing, 10 sec.) Plastic			260°C	
Soldering Information				·	
Dual-In-Line Package	Soldering (10 seconds)	260°C	260°C	260°C	
Small Outline Package	Vapor Phase (60 seconds)	215°C	215°C	215°C	
0	Infrared (15 seconds)	220°C	220°C	220°C	
See AN-450 "Surface Mou	nting Methods and Their Effect on Product	Reliability" for other methods	of soldering surface	mountdevices.	
ESD tolerance (5)		500V	500V 500V		

(1) Refer to RETS 148X for LM148 military specifications.

(2) If Military/Aerospace specified devices are required, please contact the TI Sales Office/Distributors for availability and specifications.

(3) Any of the amplifier outputs can be shorted to ground indefinitely; however, more than one should not be simultaneously shorted as the maximum junction temperature will be exceeded.

(4) The maximum power dissipation for these devices must be derated at elevated temperatures and is dictated by T<sub>JMAX</sub>, θ<sub>JA</sub>, and the ambient temperature, T<sub>A</sub>. The maximum available power dissipation at any temperature is P<sub>d</sub> = (T<sub>JMAX</sub> - T<sub>A</sub>)/θ<sub>JA</sub> or the 25°C P<sub>DMAX</sub>, whichever is less.

(5) Human body model,  $1.5 \text{ k}\Omega$  in series with 100 pF.

#### **Electrical Characteristics**

Parameter	Conditions		LM148	3	LM248			LM348			Units
Parameter	Conditions	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
Input Offset Voltage	$T_A = 25^{\circ}C, R_S \le 10 \text{ k}\Omega$		1.0	5.0		1.0	6.0		1.0	6.0	mV
Input Offset Current	$T_A = 25^{\circ}C$		4	25		4	50		4	50	nA
Input Bias Current	$T_A = 25^{\circ}C$		30	100		30	200		30	200	nA
Input Resistance	$T_A = 25^{\circ}C$	0.8	2.5		0.8	2.5		0.8	2.5		MΩ
Supply Current All Amplifiers	$T_A = 25^{\circ}C, V_S = \pm 15V$		2.4	3.6		2.4	4.5		2.4	4.5	mA
Large Signal Voltage Gain	$T_A = 25^{\circ}C, V_S = \pm 15V$ $V_{OUT} = \pm 10V, R_L \ge 2 k\Omega$	50	160		25	160		25	160		V/mV
Amplifier to Amplifier Coupling	$T_A = 25^{\circ}C$ , f = 1 Hz to 20 kHz (Input Referred) See Crosstalk Test Circuit		-120			-120			-120		dB
Small Signal Bandwidth	T <sub>A</sub> = 25°C, LM148 Series		1.0			1.0			1.0		MHz
Phase Margin	$T_A = 25^{\circ}C,$ LM148 Series (A <sub>V</sub> = 1)		60			60			60		degrees

(1) These specifications apply for  $V_S = \pm 15V$  and over the absolute maximum operating temperature range ( $T_L \le T_A \le T_H$ ) unless otherwise noted.



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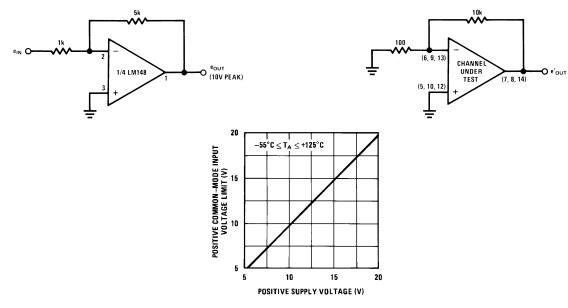
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### **Electrical Characteristics (continued)**

Demonstration			LM148	3	LM248			LM348			Units
Parameter	Conditions	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
Slew Rate	$T_A = 25^{\circ}C,$ LM148 Series (A <sub>V</sub> = 1)		0.5			0.5			0.5		V/µs
Output Short Circuit Current	$T_A = 25^{\circ}C$		25			25			25		mA
Input Offset Voltage	R <sub>S</sub> ≤ 10 kΩ			6.0			7.5			7.5	mV
Input Offset Current				75			125			100	nA
Input Bias Current				325			500			400	nA
Large Signal Voltage Gain	$V_{S} = \pm 15V, V_{OUT} = \pm 10V,$ $R_{L} > 2 k\Omega$	25			15			15			V/mV
Output Voltage Swing	$V_{\rm S} = \pm 15 V$ , $R_{\rm L} = 10 \ k\Omega$	±12	±13		±12	±13		±12	±13		V
	$R_L = 2 k\Omega$	±10	±12		±10	±12		±10	±12		V
Input Voltage Range	$V_{\rm S} = \pm 15 V$	±12			±12			±12			V
Common-Mode Rejection Ratio	R <sub>S</sub> ≤ 10 kΩ	70	90		70	90		70	90		dB
Supply Voltage Rejection	$R_S \le 10 \text{ k}\Omega, \pm 5V \le V_S \le \pm 15V$	77	96		77	96		77	96		dB

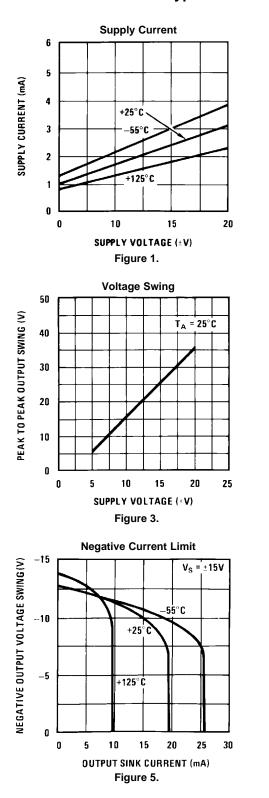
### **CROSS TALK TEST CIRCUIT**

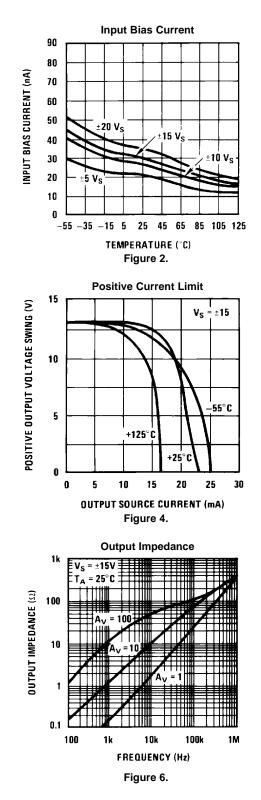
 $V_{S} = \pm 15V$ 



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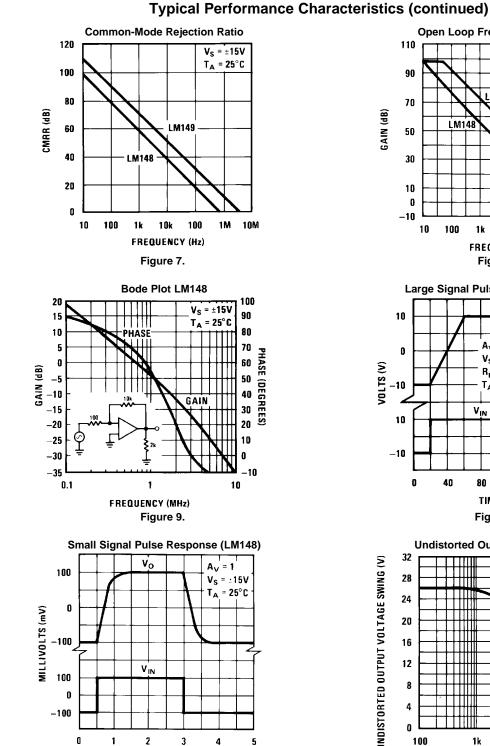
**Typical Performance Characteristics** 





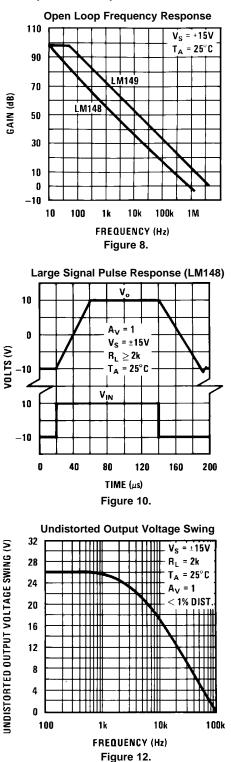
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TIME (µs)

Figure 11.



Texas

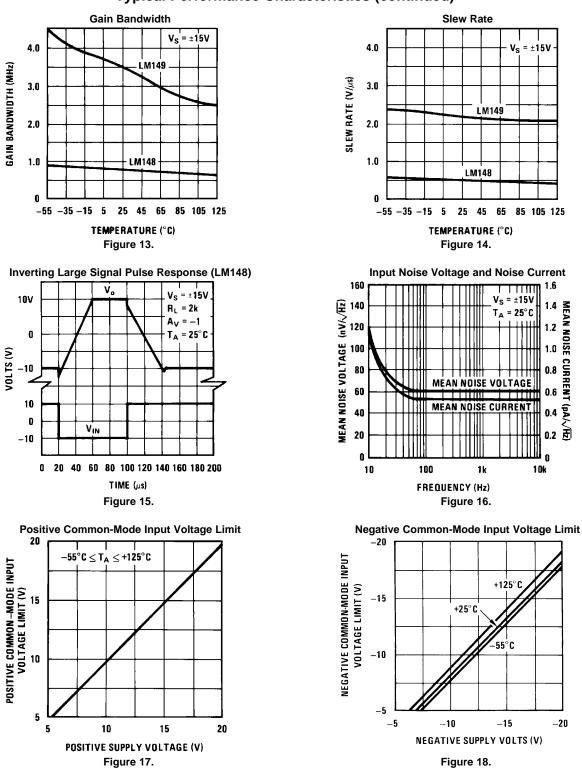
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#### **APPLICATION HINTS**

The LM148 series are quad low power 741 op amps. In the proliferation of quad op amps, these are the first to offer the convenience of familiar, easy to use operating characteristics of the 741 op amp. In those applications where 741 op amps have been employed, the LM148 series op amps can be employed directly with no change in circuit performance.

The package pin-outs are such that the inverting input of each amplifier is adjacent to its output. In addition, the amplifier outputs are located in the corners of the package which simplifies PC board layout and minimizes package related capacitive coupling between amplifiers.

The input characteristics of these amplifiers allow differential input voltages which can exceed the supply voltages. In addition, if either of the input voltages is within the operating common-mode range, the phase of the output remains correct. If the negative limit of the operating common-mode range is exceeded at both inputs, the output voltage will be positive. For input voltages which greatly exceed the maximum supply voltages, either differentially or common-mode, resistors should be placed in series with the inputs to limit the current.

Like the LM741, these amplifiers can easily drive a 100 pF capacitive load throughout the entire dynamic output voltage and current range. However, if very large capacitive loads must be driven by a non-inverting unity gain amplifier, a resistor should be placed between the output (and feedback connection) and the capacitance to reduce the phase shift resulting from the capacitive loading.

The output current of each amplifier in the package is limited. Short circuits from an output to either ground or the power supplies will not destroy the unit. However, if multiple output shorts occur simultaneously, the time duration should be short to prevent the unit from being destroyed as a result of excessive power dissipation in the IC chip.

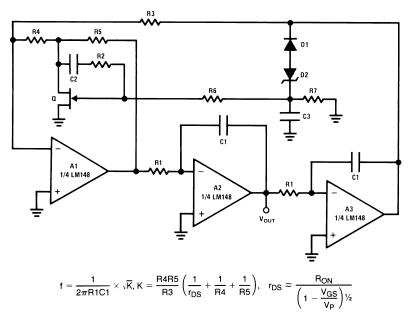
As with most amplifiers, care should be taken lead dress, component placement and supply decoupling in order to ensure stability. For example, resistors from the output to an input should be placed with the body close to the input to minimize "pickup" and maximize the frequency of the feedback pole which capacitance from the input to ground creates.

A feedback pole is created when the feedback around any amplifier is resistive. The parallel resistance and capacitance from the input of the device (usually the inverting input) to AC ground set the frequency of the pole. In many instances the frequency of this pole is much greater than the expected 3 dB frequency of the closed loop gain and consequently there is negligible effect on stability margin. However, if the feedback pole is less than approximately six times the expected 3 dB frequency a lead capacitor should be placed from the output to the input of the op amp. The value of the added capacitor should be such that the RC time constant of this capacitor and the resistance it parallels is greater than or equal to the original feedback pole time constant.

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### **Typical Applications—LM148**



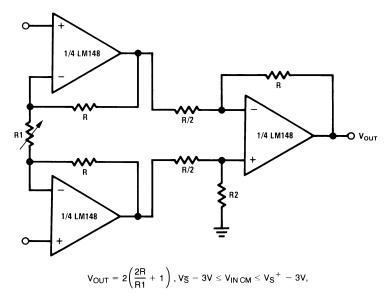


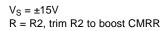
 $f_{MAX} = 5 \text{ kHz}, \text{ THD} \le 0.03\%$ 

R1 = 100k pot. C1 = 0.0047  $\mu$ F, C2 = 0.01  $\mu$ F, C3 = 0.1  $\mu$ F, R2 = R6 = R7 = 1M, R3 = 5.1k, R4 = 12 $\Omega$ , R5 = 240 $\Omega$ , Q = NS5102, D1 = 1N914, D2 = 3.6V avalanche diode (ex. LM103), V<sub>S</sub> = ±15V

A simpler version with some distortion degradation at high frequencies can be made by using A1 as a simple inverting amplifier, and by putting back to back zeners in the feedback loop of A3.







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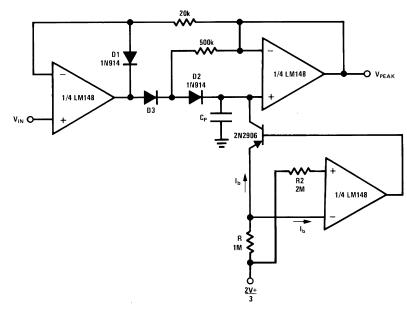
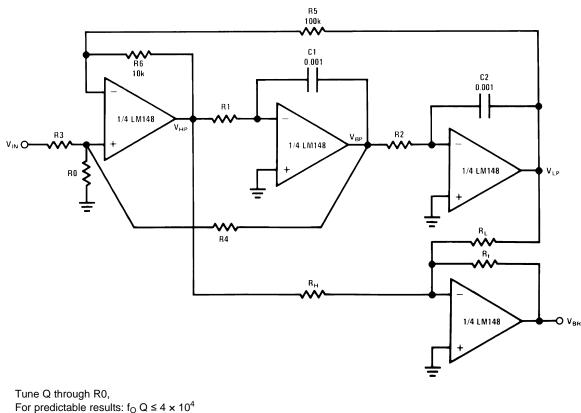


Figure 21. Low Drift Peak Detector with Bias Current Compensation

Adjust R for minimum drift D3 low leakage diode D1 added to improve speed  $V_S = \pm 15V$ 





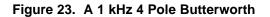
Use Band Pass output to tune for Q

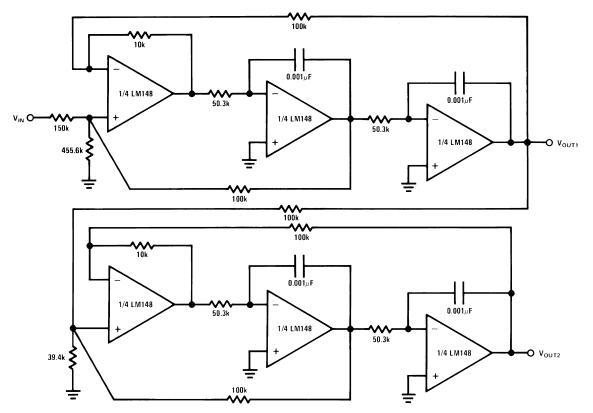
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$$\begin{split} \frac{V_{(s)}}{V_{IN(s)}} &= \frac{N_{(s)}}{D_{(s)}}, \ D(s) = S^2 + \frac{S\omega_0}{Q} + \omega_0^2 \\ N_{HP(s)} &= S^2 \, H_{OHP}, \ N_{BP(s)} = \frac{-s\omega_0 \, H_{OBP}}{Q} \quad N_{LP} = \omega_0^2 \, H_{OLP}. \\ f_o &= \frac{1}{2\pi} \sqrt{\frac{R6}{R5}} \sqrt{\frac{1}{112}}, \ t_i = R_i C_i, \ Q = \left(\frac{1 + R4|R3 + R4|R0}{1 + R6|R5}\right) \left(\frac{R6}{R5} \frac{t_1}{t_2}\right)^{\frac{1}{2}} \\ f_{NOTCH} &= \frac{1}{2\pi} \left(\frac{R_H}{R_L t_1 t_2}\right)^{\frac{1}{2}}, \ H_{OHP} = \frac{1 + R6|R5}{1 + R3|R0 + R3|R4}, \ H_{OBP} = \frac{1 + R4|R3 + R4|R0}{1 + R3|R0 + R3|R4} \\ H_{OLP} &= \frac{1 + R5|R6}{1 + R3|R0 + R3|R4} \end{split}$$

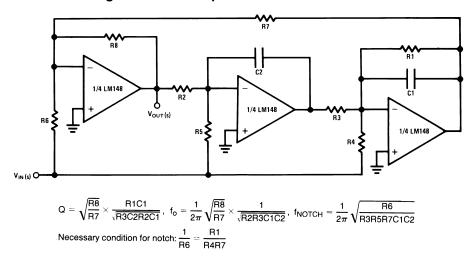




Use general equations, and tune each section separately  $Q_{1stSECTION}$  = 0.541,  $Q_{2ndSECTION}$  = 1.306 The response should have 0 dB peaking



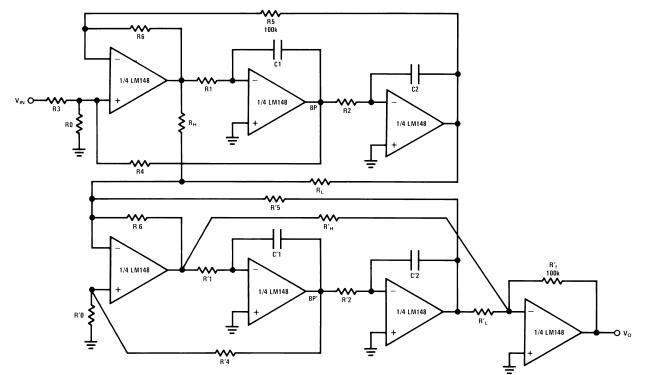
Figure 24. A 3 Amplifier Bi-Quad Notch Filter



Ex:  $f_{NOTCH} = 3 \text{ kHz}$ , Q = 5, R1 = 270k, R2 = R3 = 20k, R4 = 27k, R5 = 20k, R6 = R8 = 10k, R7 = 100k, C1 = C2 = 0.001  $\mu$ F

Better noise performance than the state-space approach.





 $\begin{array}{l} R1C1 = R2C2 = t \\ R'1C'1 = R'2C'2 = t' \\ f_C = 1 \ \text{kHz}, \ f_S = 2 \ \text{kHz}, \ f_p = 0.543, \ f_Z = 2.14, \ Q = 0.841, \ f'_P = 0.987, \ f'_Z = 4.92, \ Q' = 4.403, \ \text{normalized to ripple BW} \end{array}$ 



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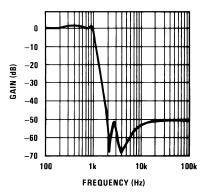
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$$f = \frac{1}{2\pi R 1C1} \times \sqrt{K}, K = \frac{R4R5}{R3} \left(\frac{1}{r_{DS}} + \frac{1}{R4} + \frac{1}{R5}\right), \quad r_{DS} \approx \frac{R_{ON}}{\left(1 - \frac{V_{GS}}{V_P}\right)^{\frac{1}{2}}}$$

Use the BP outputs to tune Q, Q', tune the 2 sections separately

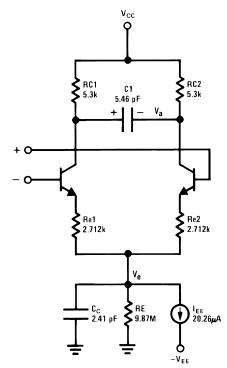
 $\begin{array}{l} R1 = R2 = 92.6k, \ R3 = R4 = R5 = 100k, \ R6 = 10k, \ R0 = 107.8k, \ R_L = 100k, \ R_H = 155.1k, \\ R'1 = R'2 = 50.9k, \ R'4 = R'5 = 100k, \ R'6 = 10k, \ R'0 = 5.78k, \ R'_L = 100k, \ R'_H = 248.12k, \ R'f = 100k. \\ \begin{array}{l} All \ capacitors \\ are \ 0.001 \ \mu F. \end{array}$ 





**Typical Simulation** 

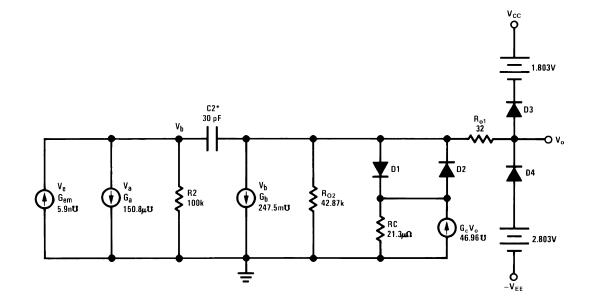
Figure 27. LM148, LM741 Macromodel for Computer Simulation



For more details, see IEEE Journal of Solid-State Circuits, Vol. SC-9, No. 6, December 1974  $_{o1} = 112I_S = 8 \times 10^{-16}$  $_{o2} = 144^*C2 = 6 \text{ pF for LM149}$ 



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**Connection Diagram** 

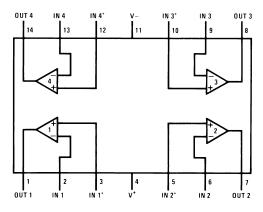


Figure 28. Top View See Package Number J0014A, D0014A or NFF00014A



#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	•		Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing			(2)		(3)		(4)	
LM148J/PB	ACTIVE	CDIP	J	14	25	TBD	A42 SNPB	Level-1-NA-UNLIM		LM148J	Samples
LM348M	ACTIVE	SOIC	D	14	55	TBD	CU SNPB	Level-1-235C-UNLIM	0 to 70	LM348M	Samples
LM348M/NOPB	ACTIVE	SOIC	D	14	55	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	0 to 70	LM348M	Samples
LM348MX	ACTIVE	SOIC	D	14	2500	TBD	CU SNPB	Level-1-235C-UNLIM	0 to 70	LM348M	Samples
LM348MX/NOPB	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	0 to 70	LM348M	Samples
LM348N/NOPB	ACTIVE	PDIP	NFF	14	25	Green (RoHS & no Sb/Br)	CU SN	Level-1-NA-UNLIM	0 to 70	LM348N	Samples
LM348N/PB	ACTIVE	PDIP	NFF	14	25	TBD	CU SNPB	Level-1-NA-UNLIM		LM348N	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> Only one of markings shown within the brackets will appear on the physical device.



24-Jan-2013

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# PACKAGE MATERIALS INFORMATION

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#### TAPE AND REEL INFORMATION





### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM348MX	SOIC	D	14	2500	330.0	16.4	6.5	9.35	2.3	8.0	16.0	Q1
LM348MX/NOPB	SOIC	D	14	2500	330.0	16.4	6.5	9.35	2.3	8.0	16.0	Q1

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# PACKAGE MATERIALS INFORMATION

17-Nov-2012



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM348MX	SOIC	D	14	2500	349.0	337.0	45.0
LM348MX/NOPB	SOIC	D	14	2500	349.0	337.0	45.0

J (R-GDIP-T\*\*) 14 LEADS SHOWN

CERAMIC DUAL IN-LINE PACKAGE

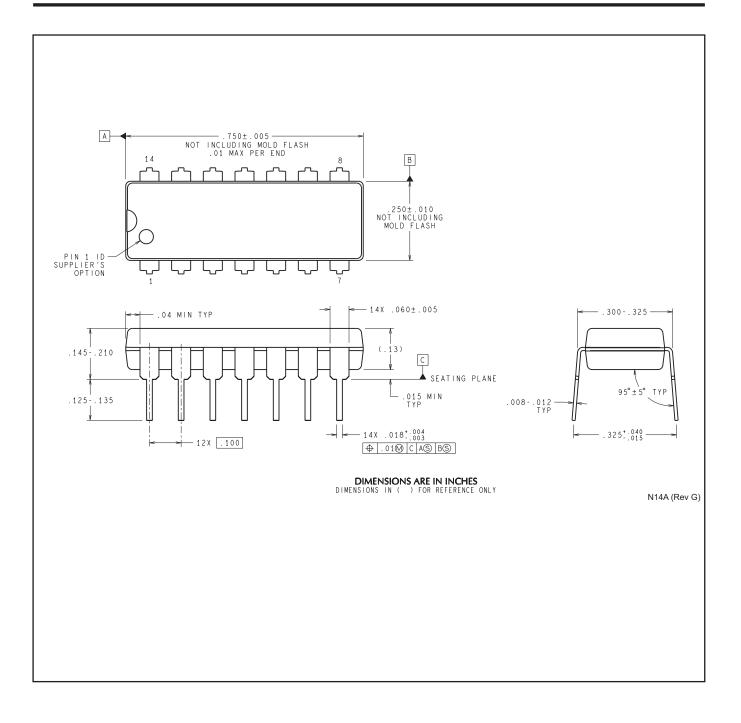


NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

# **MECHANICAL DATA**

## NFF0014A





D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



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